

NPN MJ4033 - MJ4034 - MJ4035

MEDIUM POWER COMPLEMENTARY SILICON TRANSISTORS

They are silicon epitaxial-base NPN power transistors in monolithic Darlington configuration and are mounted in Jedec TO-3 metal case.

They are intented for use as output devices in complementary general purpose amplifier applications.

The complementary PNP types are the MJ4030, MJ4031, MJ4032. Compliance to RoHS

ABSOLUTE MAXIMUM RATINGS

Symbol	R	atings		Value	Unit
			MJ4033	60	
V _{CBO}	Collector-Base Voltage	I _E =0	MJ4034	80	V
			MJ4035	100	
			MJ4033	60	
V _{CEO}	Collector-EmitterVoltage	I _B =0	MJ4034	80	V
			MJ4035	100	
			MJ4033		
V _{EBO}	Emitter-Base Voltage	I _C =0	MJ4034	5.0	V
	_		MJ4035		
I _C	Collector Current			16	А
I _B	Base Current			0.5	А
Ρ _Τ	Power Dissipation	@ T _C < 25°		150	W
TJ	Junction Temperature		200	Ĵ	
Ts	Storage Temperature			-65 to +200	U

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJ-C}	Thermal Resistance, Junction to Case1.17°C/V		°C/W



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ELECTRICAL CHARACTERISTICS

TC=25℃ unless otherwise noted

Symbol	Ratings	Test Conditi	on(s)	Min	Тур	Max	Unit
	Collector-Emitter		MJ4033	60	-	-	
V _{CEO}	Voltage (*)	I _C =100 mA, I _B =0	MJ4034	80	-	- '	V
			MJ4035	100			
	Collector Cutoff Current	V_{CE} =30 Vdc, I _B =0	MJ4033	-	-	3.0 m	
I _{CEO}		V _{CE} =40 Vdc, I _B =0	MJ4034	-	-		mA
		V _{CE} =50 V, I _B =0	MJ4035	-	-		
			MJ4033				mA
I _{EBO}	Emitter Cutoff Current	V _{BE} =5.0 V, I _C =0	MJ4034	-	-	5.0	
			MJ4035				
		V _{CB} =60 V	MJ4033	-	-	1.0	mAdc
		R _{BE} =1.0 kΩ	10134033				
	Collector-Emitter Leakage Current	V _{CB} =80 V	MJ4034	-	-		
		R_{BE} =1.0 k Ω					
		V _{CB} =100 V	MJ4035				
		R _{BE} =1.0 kΩ					
		V _{CB} =60 V	MJ4033	-	-	5.0	
		R _{BE} =1.0 kΩ					
		T _c =150℃					
		V _{CB} =80 V					
		R _{BF} =1.0 kΩ	MJ4034	-			
		T _c =150℃					
		V _{CB} =100 V					
		R _{BE} =1.0 kΩ	MJ4035				
		T _c =150℃					
			MJ4033			2.5	
V _{CE(SAT)}		$I_{c}=10 \text{ A}$	MJ4034	-	-		
	Collector-Emitter saturation	I _B =40 mA	MJ4035				Vala
	Voltage (*)	(*) $I_{C}=16 \text{ A} $ MJ4033 $I_{B}=80 \text{ mA} $ MJ4034 MJ4035			Vdc		
			MJ4034		4.0		
V _{BE}	Base-Emitter Voltage (*)	$I_{c}=10 \text{ A}$	MJ4033	3 4 -	-	3	V
			MJ4034				
			MJ4035				
	DC Current Gain (*)	V _{CE} =10 V I _C =3.0 A	MJ4033	1000		-	-
h _{FE}			MJ4034		-		
•••••			MJ4035				

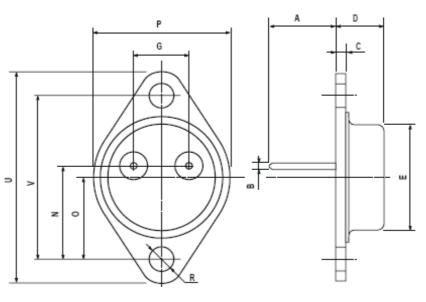
(*) Pulse Width $\approx 300~\mu s,$ Duty Cycle $\angle~2.0\%$



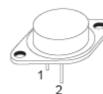
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)			
	min	max	
A	11	13.10	
В	0.97	1.15	
С	1.5	1.65	
D	8.32	8.92	
F	19	20	
G	10.70	11.1	
N	16.50	17.20	
Р	25	26	
R	4	4.09	
U	38.50	39.30	
V	30	30.30	



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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